



General Description

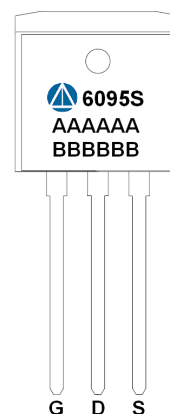
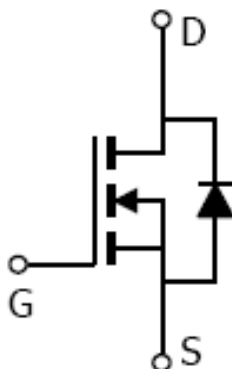
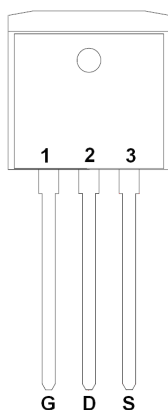
AFN6095S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 60V/40A, $R_{DS(ON)} = 7.8m\Omega @ V_{GS}=10V$
- 60V/25A, $R_{DS(ON)} = 9.8m\Omega @ V_{GS}=6V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- TO-262 package design

Pin Description (TO-262)



Application

- Synchronous Rectifier
- Power Supplies

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN6095ST262TG	6095S AAAAAA BBBBBB	TO-262	Tube	50 EA

- ※ A Lot code
- ※ B Date code
- ※ AFN6095ST262TG : Tube ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	60	A
		40	
Pulsed Drain Current	I _{DM}	150	
Continuous Source Current(Diode Conduction)	I _S	80	
Single Pulse Avalanche Current	I _{AS}	40	
Power Dissipation	P _D	100	W
		3.1	
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	62.5	°C/W

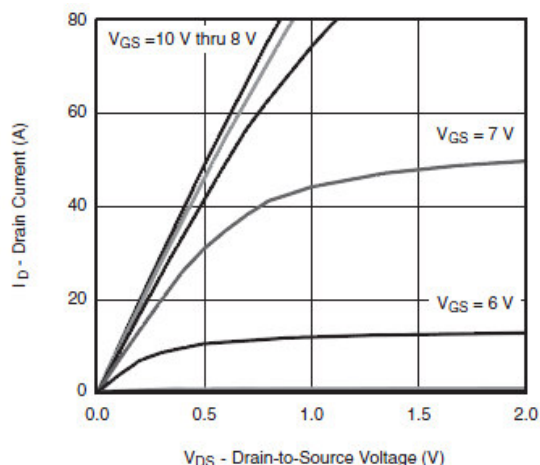
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

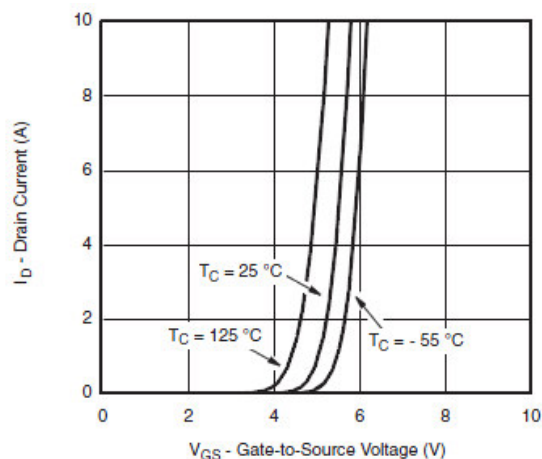
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2.0		4.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V			1	uA
		V _{DS} =48V, V _{GS} =0V T _J =85°C			30	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 10V, V _{GS} =10V	80			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =40A		6.3	7.8	mΩ
		V _{GS} =6V, I _D =25A		8	9.8	
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =15A		38		S
Diode Forward Voltage	V _{SD}	I _S =40A, V _{GS} =0V		0.8	1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =10V I _D ≡20A		35	60	nC
Gate-Source Charge	Q _{gs}			12		
Gate-Drain Charge	Q _{gd}			10		
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V f=1MHz		2080		pF
Output Capacitance	C _{oss}			320		
Reverse Transfer Capacitance	C _{rss}			120		
Turn-On Time	t _{d(on)}	V _{DD} =30V, R _L =1.53Ω I _D ≡20A, V _{GEN} =10V R _G =1.0Ω		10	20	ns
	t _r			10	20	
Turn-Off Time	t _{d(off)}			15	30	
	t _f			10	20	



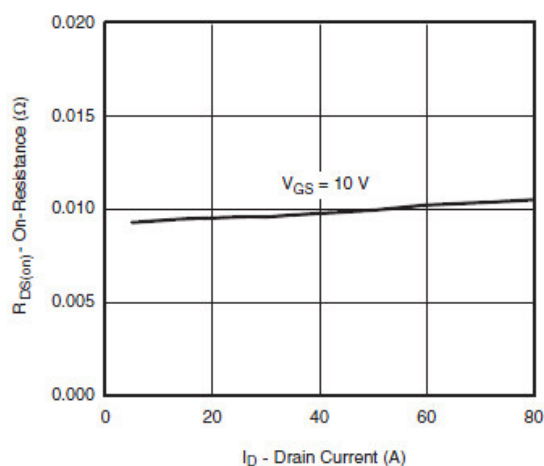
Typical Characteristics



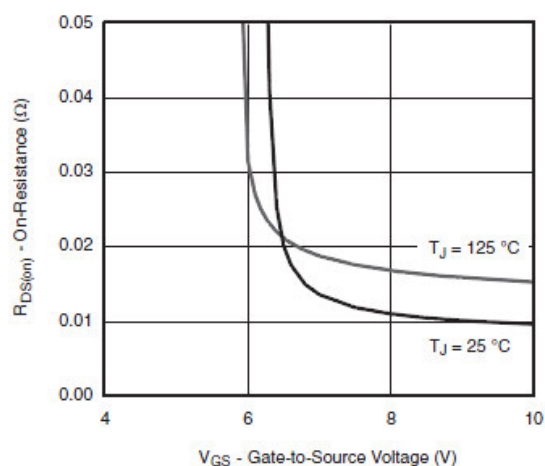
Output Characteristics



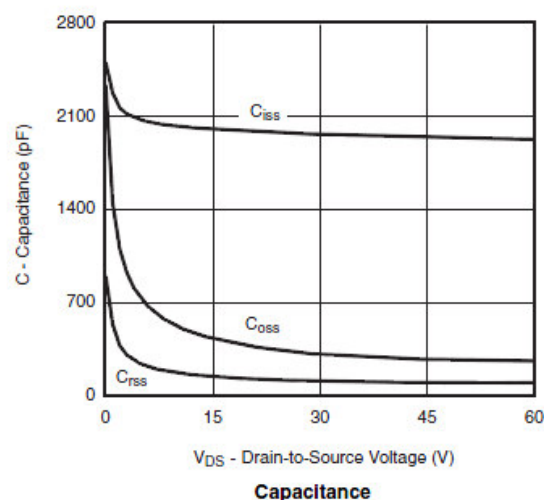
Transfer Characteristics



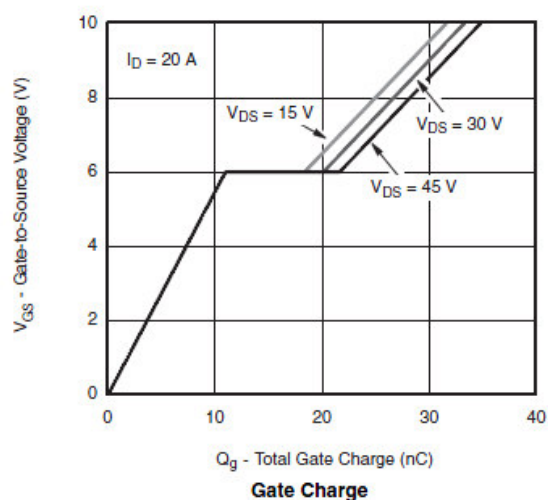
On-Resistance vs. Drain Current



On-resistance vs. Gate-to-Source Voltage



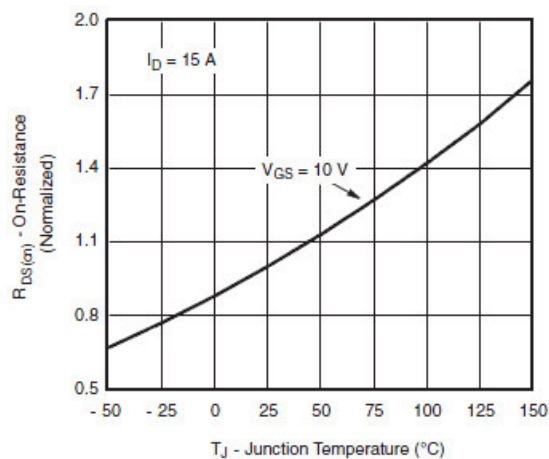
Capacitance



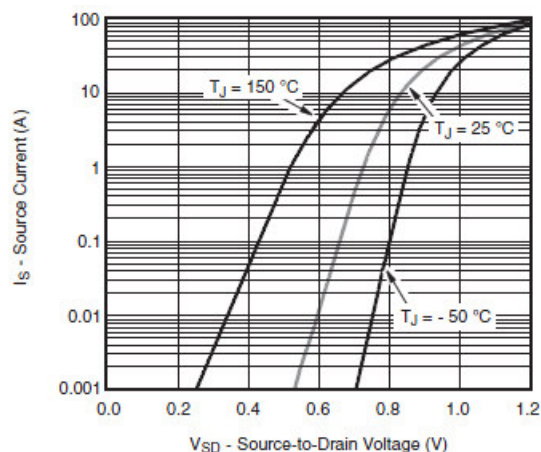
Gate Charge



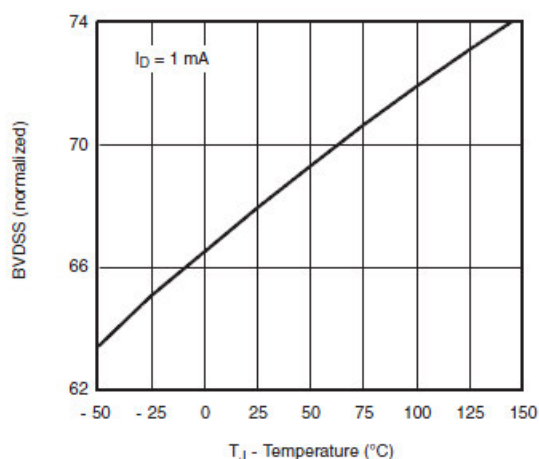
Typical Characteristics



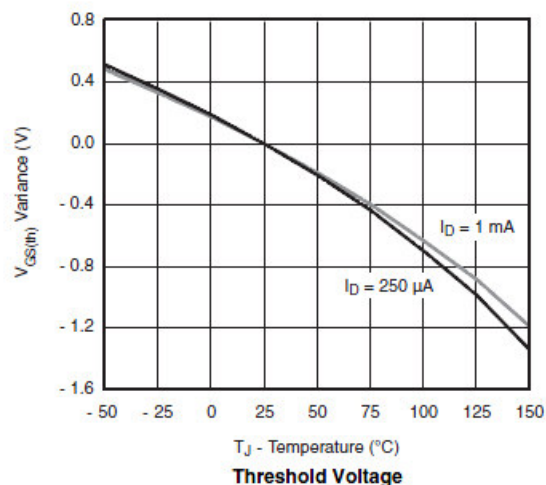
On-Resistance vs. Junction Temperature



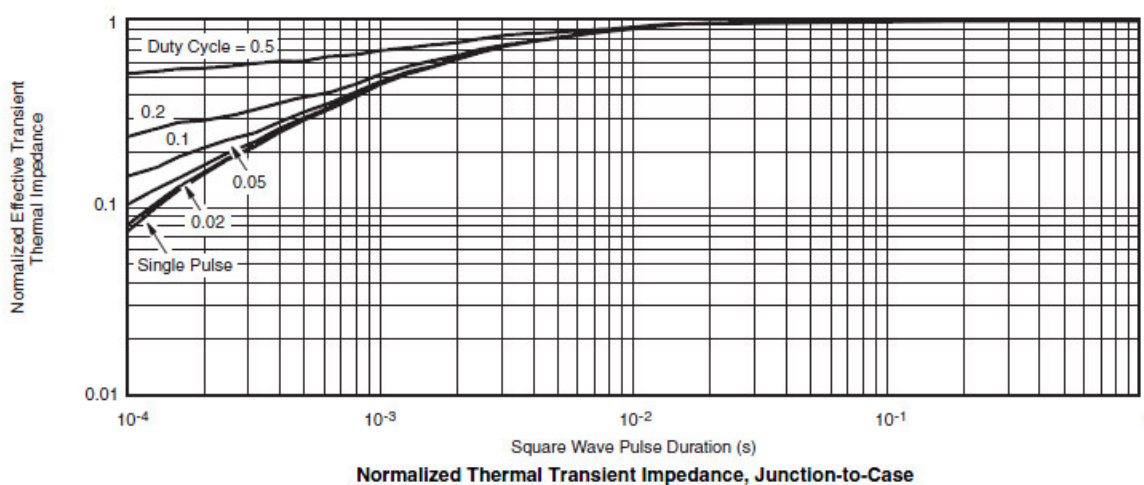
Source-Drain Diode Forward Voltage



Drain-Source Breakdown vs. Junction Temperature



Threshold Voltage

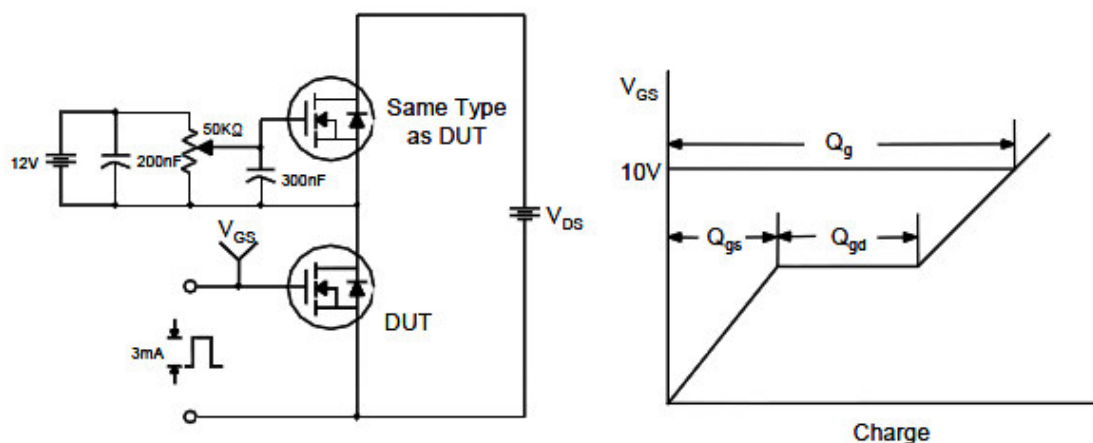


Normalized Thermal Transient Impedance, Junction-to-Case

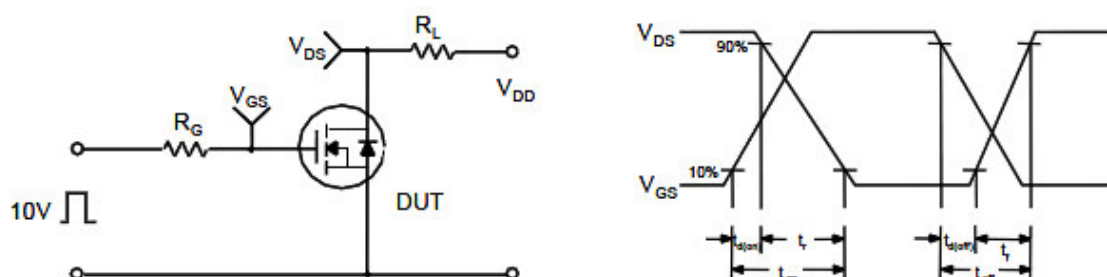


Typical Characteristics

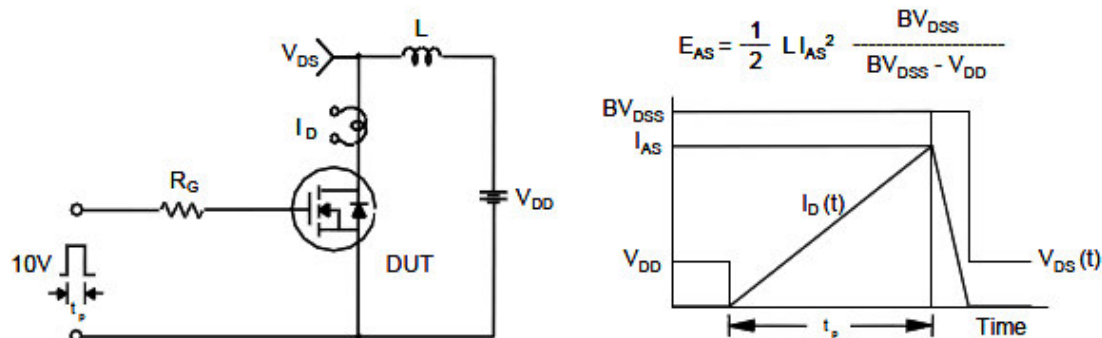
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

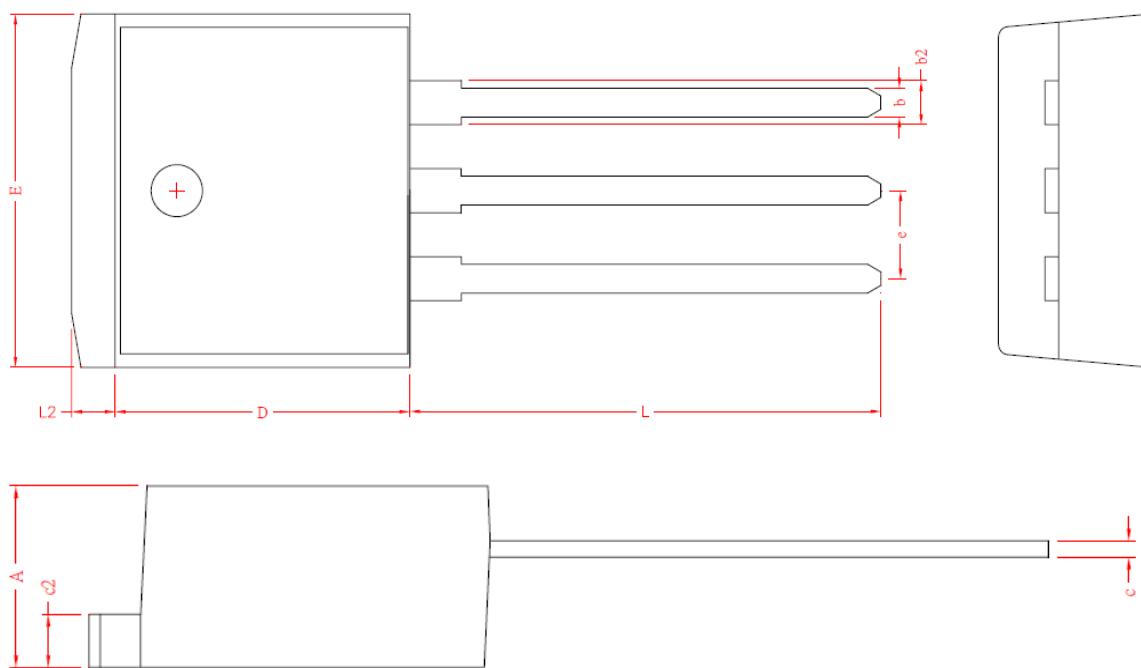


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (TO-262)



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c2	1.25	1.45
b	0.76	1.0	b2	1.17	1.47
D	8.6	9.0	L	13.25	14.25
c	0.36	0.50	e	2.54 REF.	
E	9.80	10.4	L2	1.27 REF.	

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